20

11.5

12

 $\, m\Omega$ 

Α



### **Features**

- 20V/12A
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

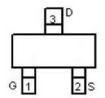
## **Applications**

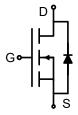
- Portable Equipment and Battery Powered Systems.
- DC-DC converter
- Load Switch

Top view



SOT23-3





**Product Summary** 

 $R_{DS(on),Typ}$ @  $V_{GS}=4.5 \text{ V}$ 

V DS

*1* D

## **Absolute Maximum Ratings** (T<sub>A</sub>=25°C Unless Otherwise Noted)

| Parameter                              | Symbol                  | Rating    | Unit |
|--|-------------------------|-----------|------|
| Drain-Source Voltage                   | V <sub>DS</sub>         | 20        | V    |
| Drain Current - Continuous             | I <sub>D</sub> (Ta=25℃) | 12        | A    |
| Drain Current - Continuous             | I <sub>D</sub> (Ta=70℃) | 4.8       | А    |
| Drain Current – Pulsed                 | I <sub>DM</sub>         | 48        | A    |
| Gate-Source Voltage                    | $V_{GS}$                | ±8.0      | V    |
| Maximum Power Dissipation              | P <sub>D</sub> (Ta=25℃) | 1.14      | W    |
| Thermal Resistance Junction-to-Ambient | $R_{	heta JA}$          | 110       | °C/W |
| Junction Temperature                   | T <sub>j</sub>          | 150       | °C   |
| Storage Temperature Range              | T <sub>stg</sub>        | -55 ~ 150 | °C   |



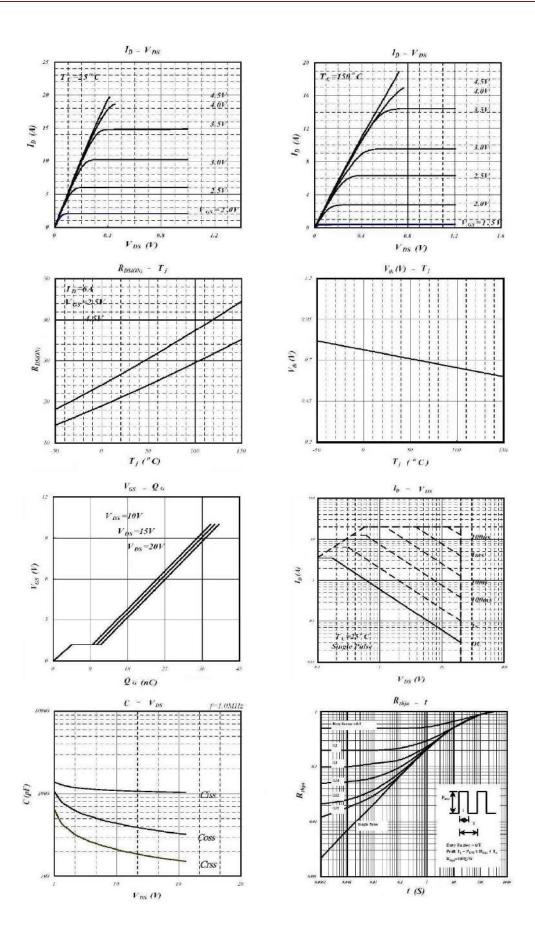
# **Electrical Characteristics** (T<sub>A</sub>=25°C Unless Otherwise Noted)

| Parameter                               | Symbol              | Test Conditions   |                       | Min  | Тур  | Max   | Unit |
|---|---------------------|---|-----------------------|------|------|-------|------|
| Drain-Source Breakdown Voltage          | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V   | I <sub>D</sub> =250µA | 20   | Тур  | IVIGX | V    |
| Drain-Source Leakage<br>Current(T =25℃) | I <sub>DSS</sub>    | V <sub>DS</sub> =16V  | V <sub>GS</sub> =0V   |      |      | 1     | μΑ   |
| Drain-Source Leakage<br>Current(T=70℃)  | I <sub>DSS</sub>    | V <sub>DS</sub> =16V  | V <sub>GS</sub> =0V   |      |      | 30    | μΑ   |
| Gate-Source Leakage Current             | I <sub>GSS</sub>    | V <sub>GS</sub> =±8V  | V <sub>DS</sub> =0V   |      |      | ±100  | nA   |
| Gate Threshold Voltage                  | $V_{GS(th)}$        | V <sub>DS</sub> =V <sub>GS</sub>  | I <sub>D</sub> =250μA | 0.55 |      | 0.95  | ٧    |
| Static Drain-Source On-Resistance       | R <sub>DS(on)</sub> | V <sub>GS</sub> =4.5V   | I <sub>D</sub> = 5 A  |      | 11.5 | 12.5  | mΩ   |
|   |                     | V <sub>GS</sub> =2.5V   | I <sub>D</sub> = 3 A  |      | 15.5 | 16.5  | mΩ   |
| Forward Transconductance                | g <sub>FS</sub>     | V <sub>DS</sub> =10V  | I <sub>D</sub> =6.0A  |      | 20   |       | S    |
| Forward On Voltage                      | V <sub>SD</sub>     | V <sub>GS</sub> =0V   | I <sub>S</sub> =1.7A  |      |      | 1.3   | V    |
| Input Capacitance                       | C <sub>iss</sub>    | V <sub>DS</sub> =20V V <sub>GS</sub> =0V f=1.0MHz   |                       |      | 1035 |       | pF   |
| Output Capacitance                      | C <sub>oss</sub>    |   |                       |      | 320  |       | pF   |
| Reverse Transfer Capacitance            | C <sub>rss</sub>    | 1.011112  |                       |      | 150  |       | pF   |
| Turn-on Delay Time                      | t <sub>d(on)</sub>  |   |                       |      | 30   |       | ns   |
| Rise Time                               | t <sub>r</sub>      | $\begin{array}{lll} V_{DS}{=}10V & I_{D}{=}1A \\ V_{GS}{=}5V & R_{G}{=}6\Omega \\ R_{D}{=}10\Omega \end{array}$ |                       |      | 70   |       | ns   |
| Turn-off Delay Time                     | t <sub>d(off)</sub> |   |                       |      | 40   |       | ns   |
| Fall Time                               | t <sub>f</sub>      |   |                       |      | 65   |       | ns   |

#### Notes:

- 1. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 2、Pulse Test: Pulse Width ≤ 300 $\mu$ s, Duty Cycle ≤2%.







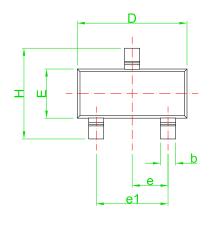
# **Ordering and Marking Information**

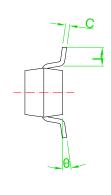
| Ordering Device No. | Marking | Package | Packing   | Quantity  |
|---------------------|---------|---------|-----------|-----------|
| JM3E20N12ZB-R       | 20N12   | SOT23-3 | Tape&Reel | 3000/Reel |

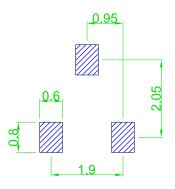
| PACKAGE | MARKING         |  |  |
|---------|-----------------|--|--|
| SOT23-3 | 20N12 Date Code |  |  |

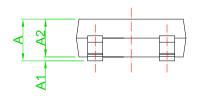


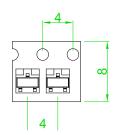
### **SOT23-3 PACKAGE IN FORMATION**











Recommended Land Pattern

| Symbol | Dimensions in Millimeters |      | Dimensions in Inches |       |  |
|--------|---------------------------|------|----------------------|-------|--|
| Symbol | Min                       | Max  | Min                  | Max   |  |
| Α      | 0.90                      | 1.15 | 0.035                | 0.045 |  |
| A1     | 0.00                      | 0.10 | 0.000                | 0.004 |  |
| A2     | 0.90                      | 1.05 | 0.035                | 0.041 |  |
| b      | 0.30                      | 0.55 | 0.012                | 0.022 |  |
| С      | 80.0                      | 0.15 | 0.003                | 0.006 |  |
| D      | 2.80                      | 3.00 | 0.110                | 0.118 |  |
| Е      | 1.20                      | 1.40 | 0.047                | 0.055 |  |
| е      | 0.95 TYP                  |      | 0.037 TYP 0.037 TYP  |       |  |
| e1     | 1.80                      | 2.00 | 0.071                | 0.079 |  |
| Н      | 2.25                      | 2.55 | 0.089                | 0.100 |  |
| L      | 0.30                      | 0.50 | 0.012                | 0.020 |  |
| θ      | 0°                        | 8°   | 0°                   | 8°    |  |



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